

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE (PCT PROCESS)

2SA1320

HIGH VOLTAGE SWITCHING APPLICATIONS

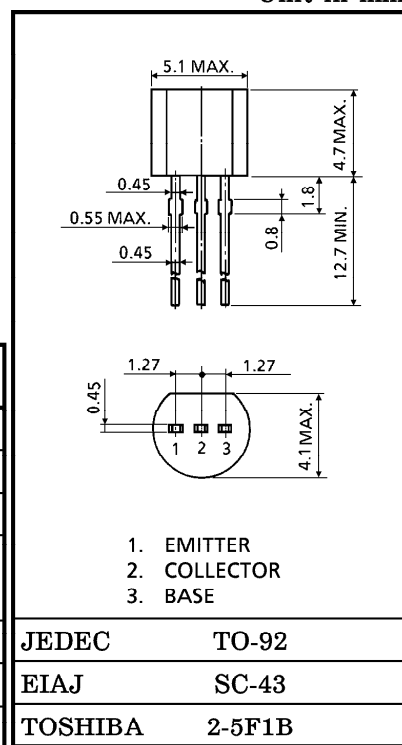
COLOR TV CHROMA OUTPUT APPLICATIONS

Unit in mm

- High Voltage : $V_{CEO} = -250V$
- Low C_{re} : 1.8pF (Max.)
- Complementary to 2SC3333

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	-250	V
Collector-Emitter Voltage		V_{CEO}	-250	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current	DC	I_C	-50	mA
	Pulsed	I_{CP}	-100	
Base Current		I_B	-20	mA
Collector Power Dissipation		P_C	0.6	W
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55~150	$^\circ C$



Weight : 0.21g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -200V, I_E = 0$	—	—	-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-250	—	—	V
DC Current Gain	h_{FE}	$V_{CE} = -20V, I_C = -25mA$	50	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$	—	—	-1.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -20V, I_C = -25mA$	—	-0.75	—	V
Transition Frequency	f_T	$V_{CE} = -10V, I_C = -10mA$	60	80	—	MHz
Reverse Transfer Capacitance	C_{re}	$V_{CB} = -30V, I_E = 0, f = 1MHz$	—	—	1.8	pF

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